

.

HOGAN & HARTSON - 81919.0017 Yoshikazu FUJIMORI, "Data Holding Device and Data Holding Method" EV 324 111 145 US Page 2 of 25

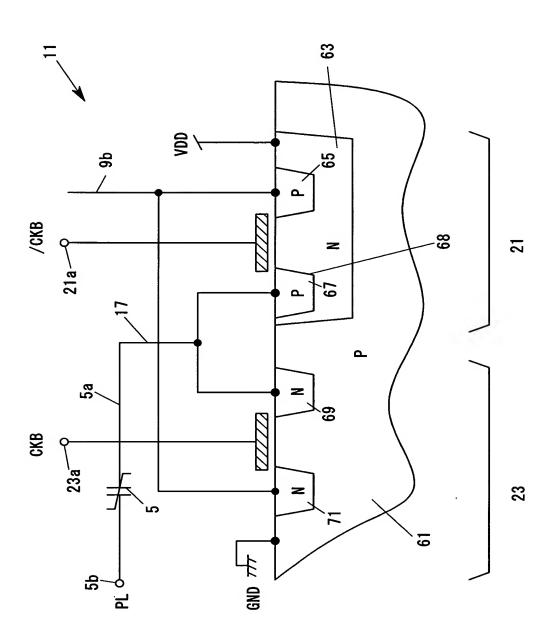


Fig. 2

HOGAN & HARTSON - 81919.0017 Yoshikazu FUJIMORI, "Data Holding Device and Data Holding Method" EV 324 111 145 US Page 3 of 25

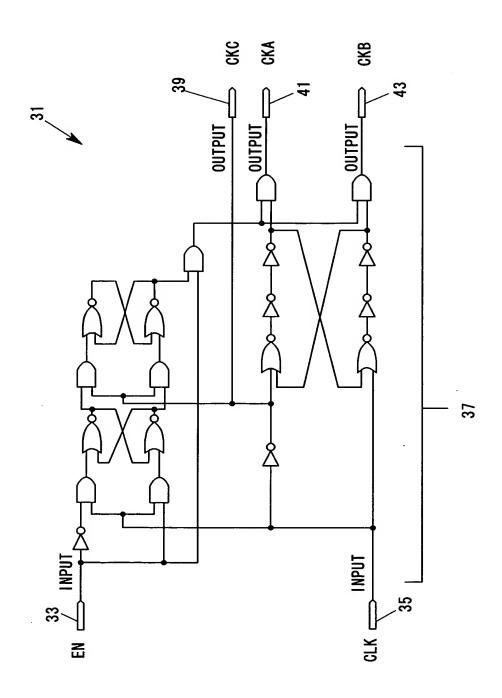


Fig. 3

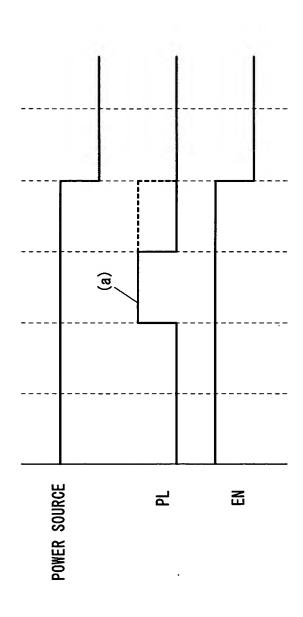


Fig. 4

HOGAN & HARTSON – 81919.0017 Yoshikazu FUJIMORI, "Data Holding Device and Data Holding Method" EV 324 111 145 US Page 5 of 25

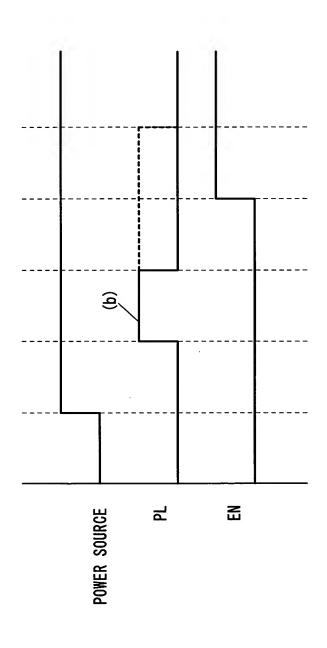


Fig. 5

HOGAN & HARTSON – 81919.0017 Yoshikazu FUJIMORI, "Data Holding Device and Data Holding Method" EV 324 111 145 US Page 6 of 25

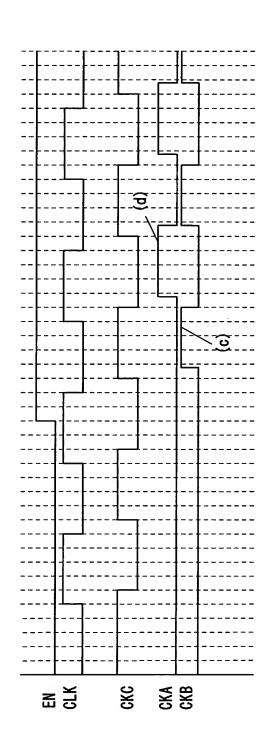


Fig. 6

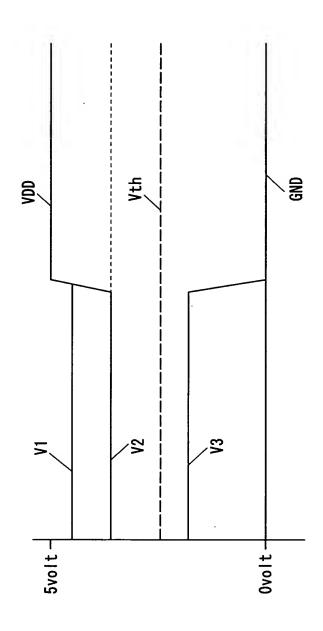


Fig. 7

HOGAN & HARTSON - 81919.0017 Yoshikazu FUJIMORI, "Data Holding Device and Data Holding Method" EV 324 111 145 US Page 8 of 25

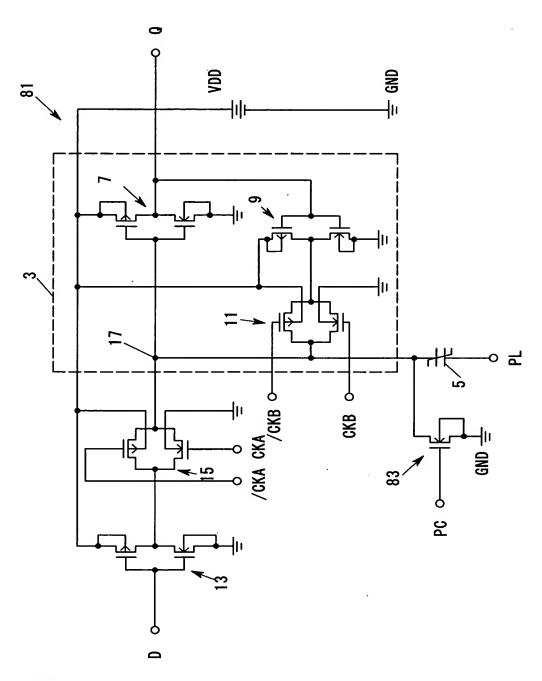


Fig. 8

HOGAN & HARTSON - 81919.0017 Yoshikazu FUJIMORI, "Data Holding Device and Data Holding Method" EV 324 111 145 US Page 9 of 25

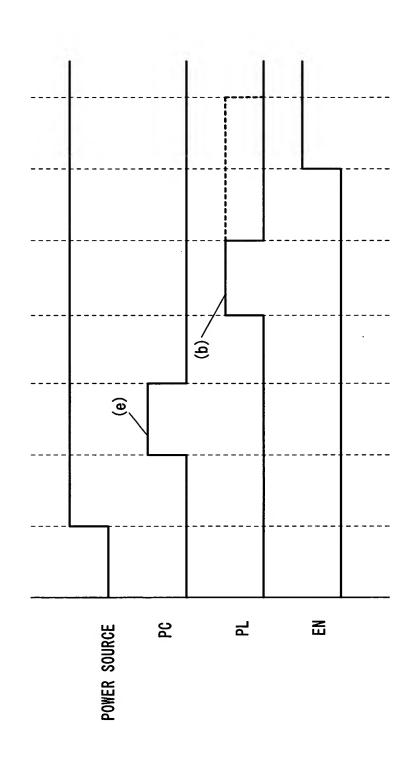
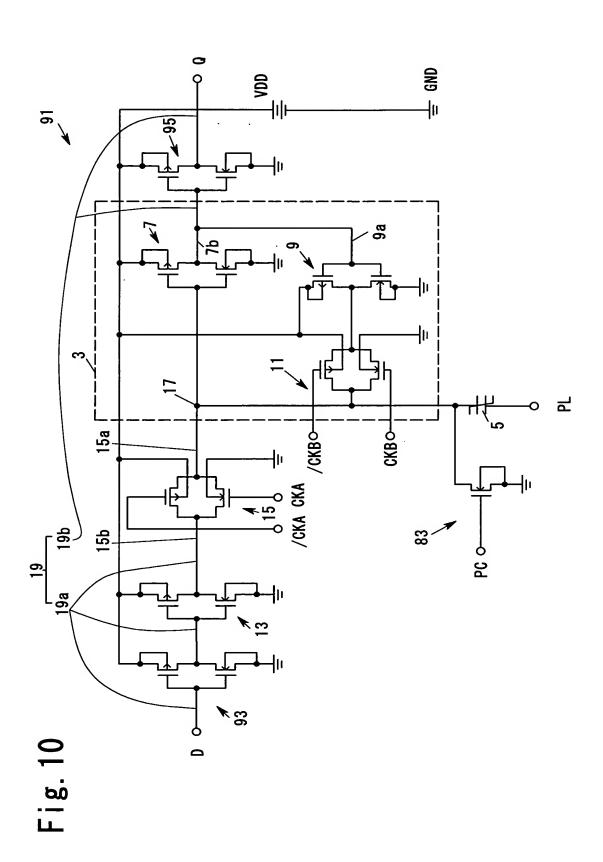
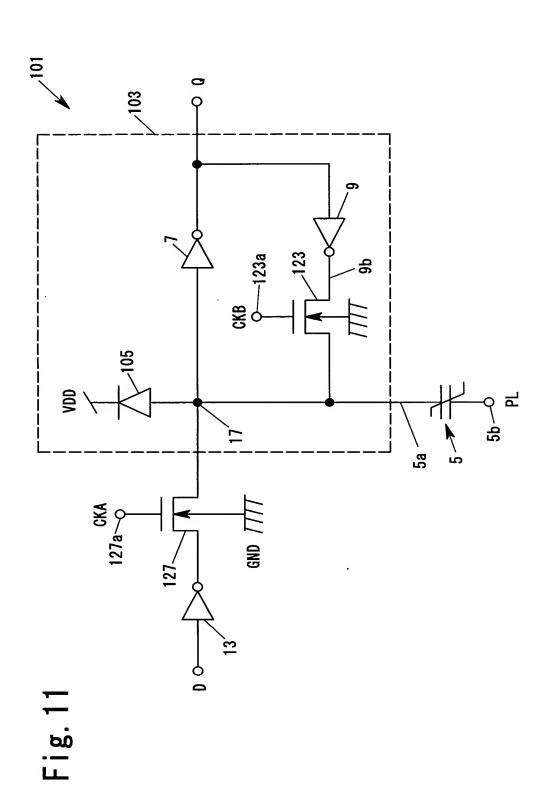


Fig. 9

HOGAN & HARTSON – 81919.0017 Yoshikazu FUJIMORI, "Data Holding Device and Data Holding Method" EV 324 111 145 US Page 10 of 25



HOGAN & HARTSON – 81919.0017 Yoshikazu FUJIMORI, "Data Holding Device and Data Holding Method" EV 324 111 145 US Page 11 of 25



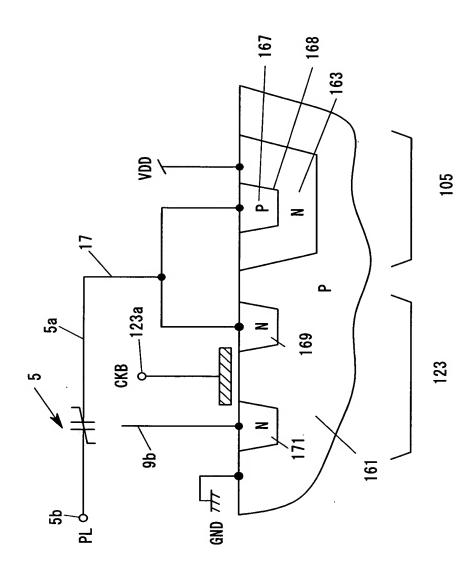
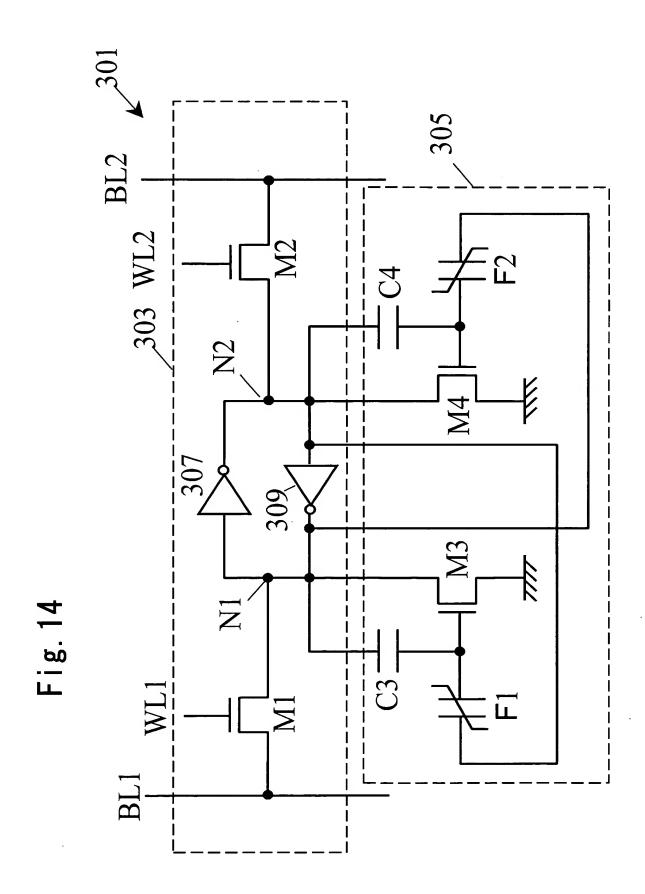


Fig. 12

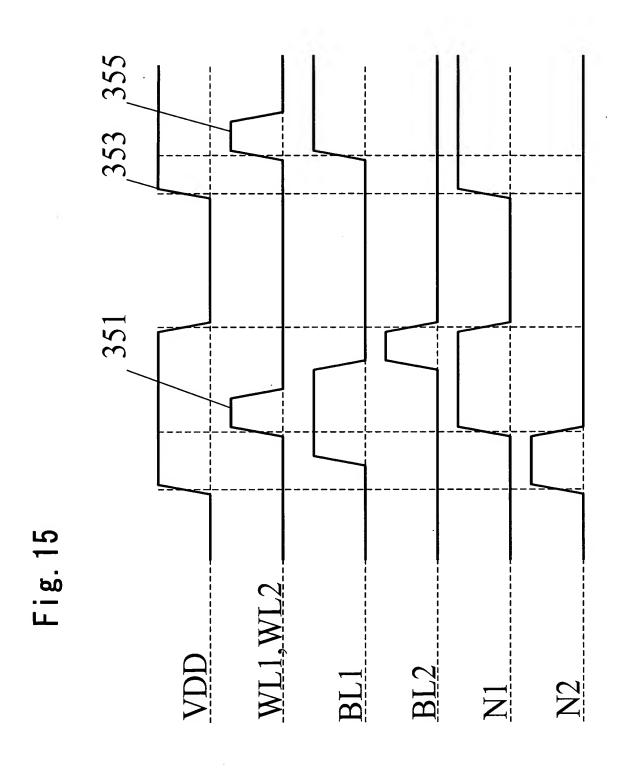
HOGAN & HARTSON - 81919.0017 Yoshikazu FUJIMORI, "Data Holding Device and Data Holding Method" EV 324 111 145 US Page 13 of 25

Fig. 130 8 205 205 Fig. 13B 205a

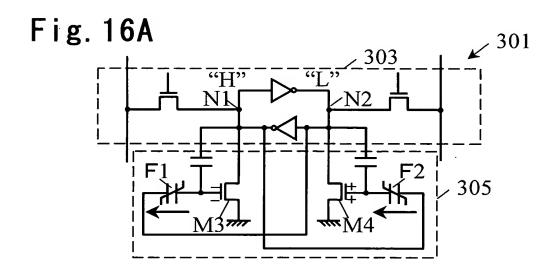
Fig. 13A

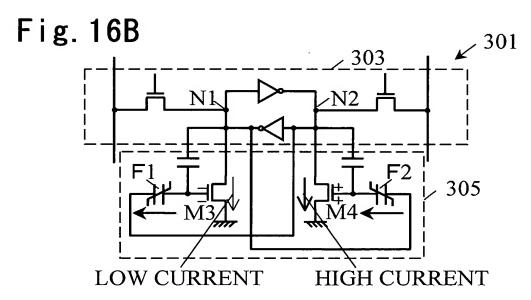


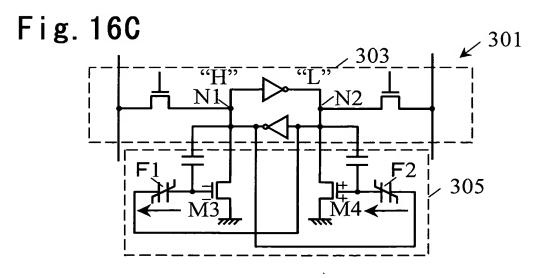
HOGAN & HARTSON - 81919.0017 Yoshikazu FUJIMORI, "Data Holding Device and Data Holding Method" EV 324 111 145 US Page 15 of 25



HOGAN & HARTSON – 81919.0017 Yoshikazu FUJIMORI, "Data Holding Device and Data Holding Method" EV 324 111 145 US Page 16 of 25







HOGAN & HARTSON - 81919.0017 Yoshikazu FUJIMORI, "Data Holding Device and Data Holding Method" EV 324 111 145 US Page 17 of 25

Fig. 17

CHARACTERISTIC OF
TRANSISTOR M4

CHARACTERISTIC OF ORIGINAL
TRANSISTOR (BROKEN LINE)
HIGH CURRENT

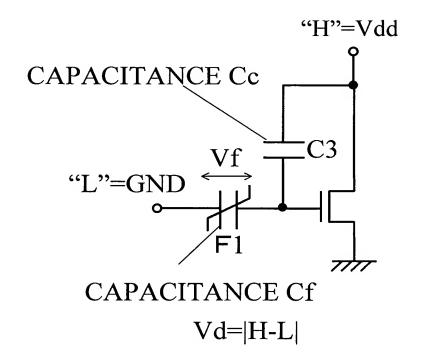
CHARACTERISTIC OF
TRANSISTOR M3

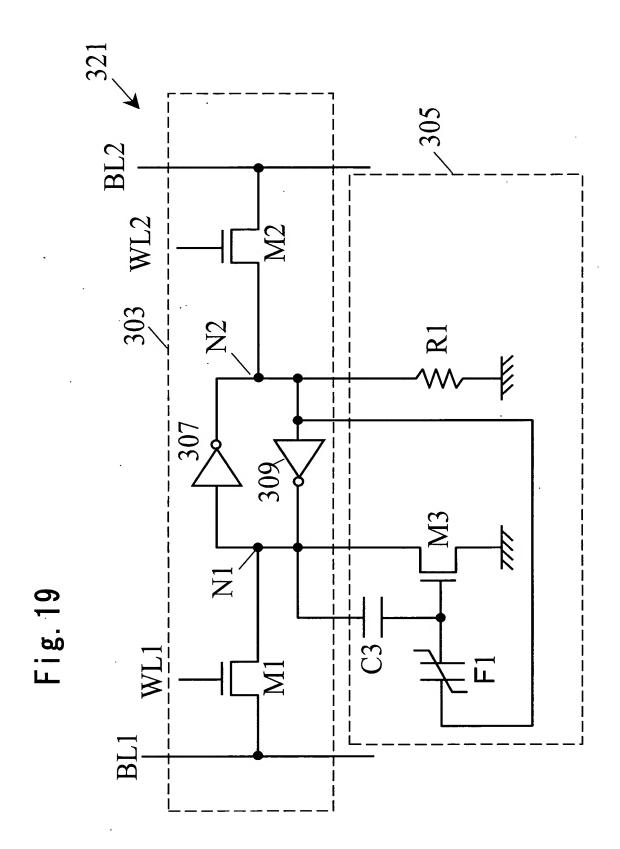
LOW CURRENT

GATE VOLTAGE

HOGAN & HARTSON - 81919.0017 Yoshikazu FUJIMORI, "Data Holding Device and Data Holding Method" EV 324 111 145 US Page 18 of 25

Fig. 18





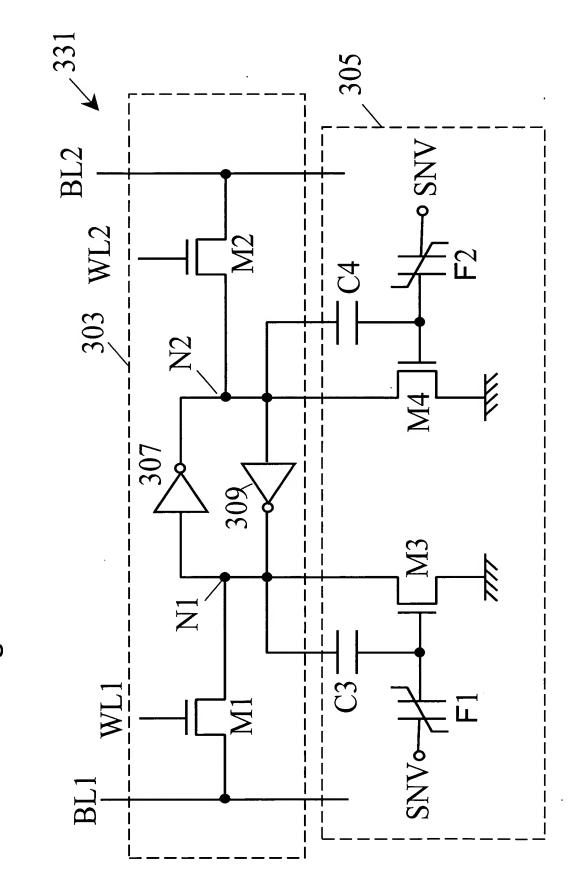
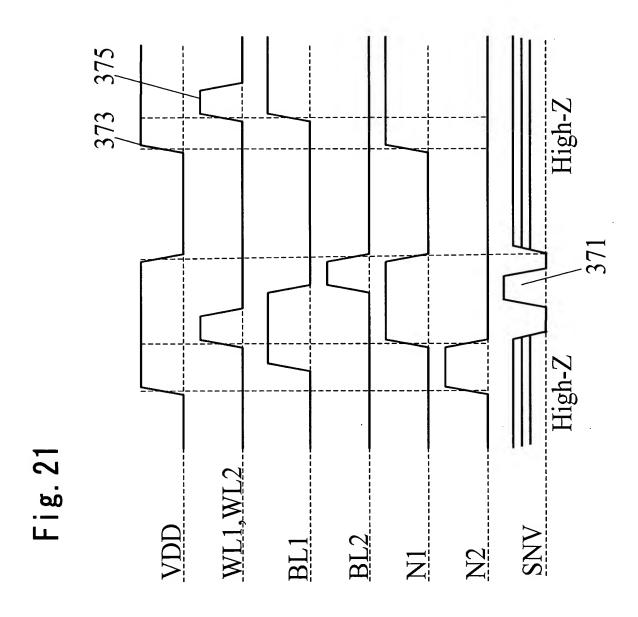
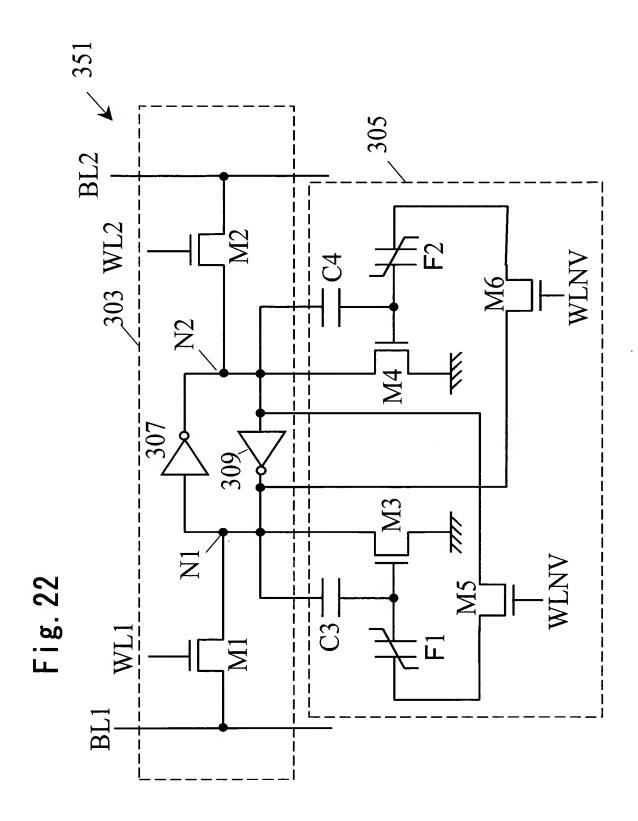
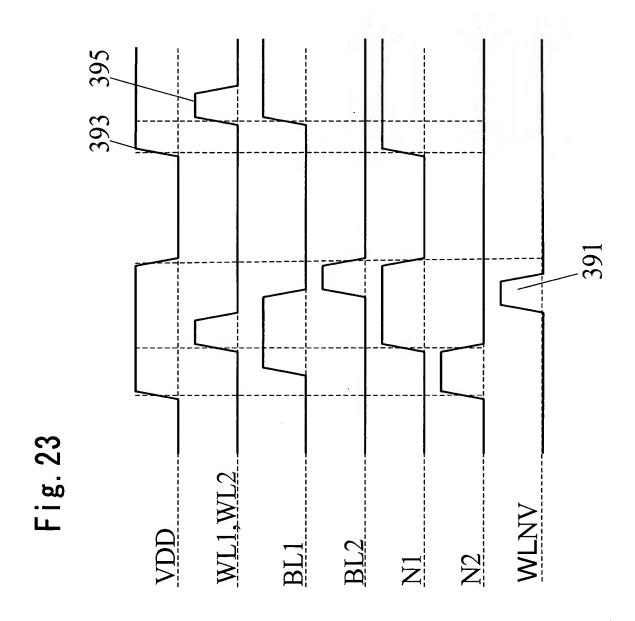


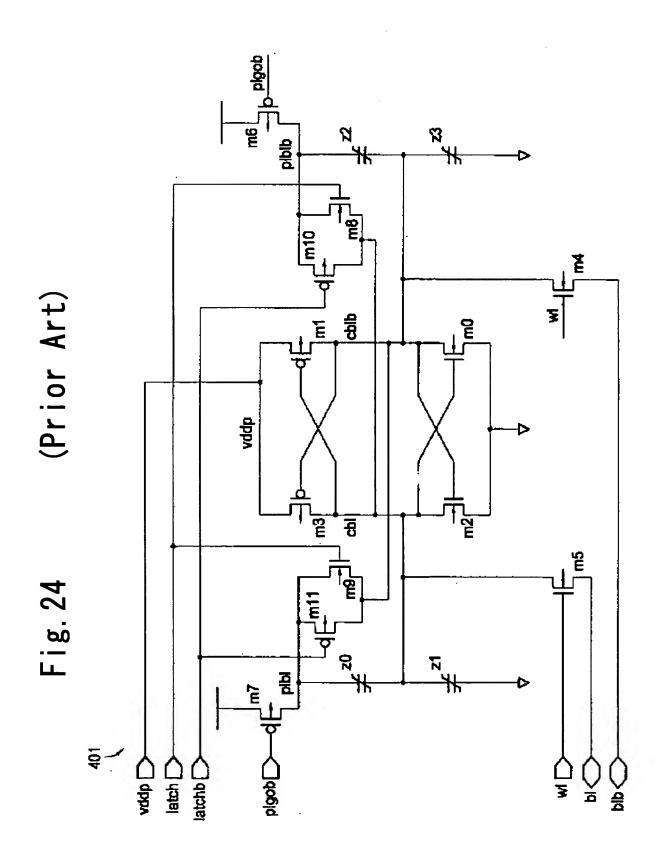
Fig. 20

HOGAN & HARTSON - 81919.0017 Yoshikazu FUJIMORI, "Data Holding Device and Data Holding Method" EV 324 111 145 US Page 21 of 25









HOGAN & HARTSON - 81919.0017 Yoshikazu FUJIMORI, "Data Holding Device and Data Holding Method" EV 324 111 145 US Page 25 of 25

